

LL10XB60HT

PRV : 600 Volts
I_o : 10 Amperes

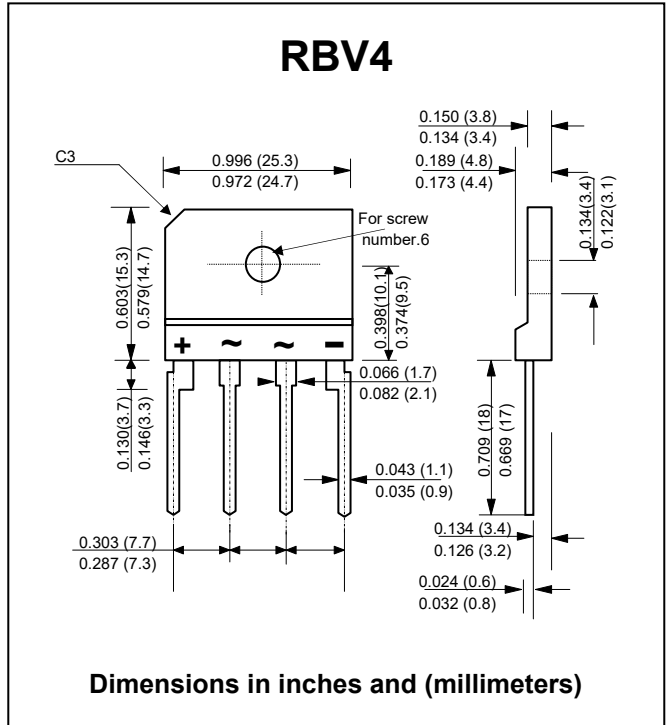
FEATURES :

- * Glass passivated junction chip
- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Ideal for printed circuit board
- * Very good heat dissipation
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : Reliable low cost construction utilizing molded plastic technique
- * Epoxy : UL94V-O rate flame retardant
- * Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Polarity symbols marked on case
- * Mounting position : Any
- * Weight : 4.28 grams

Low VF BRIDGE RECTIFIER



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

RATING	SYMBOL	VALUE	UNIT
Maximum Peak Reverse Voltage	V _{RM}	600	V
Maximum Average Forward Current (50Hz Sine wave, R-load)	I _o	10 3	A
Maximum Peak Forward Surge Current, T _J = 25 °C (50Hz sine wave, Non-repetitive 1 cycle peak value)	I _{FSM}	120	A
Current Squared Time at 1ms ≤ t < 10 ms, T _J = 25 °C	I ² t	60	A ² S
Maximum Forward Voltage per Diode at I _F = 5.0 A (Pulse measurement, Rating of per diode)	V _F	0.92	V
Maximum DC Reverse Current, V _R =V _{RM} (Pulse measurement, Rating of per diode)	I _R	10	μA
Maximum Thermal Resistance, Junction to case, With heatsink	R _{θJC}	2.3	°C/W
Maximum Thermal Resistance, Junction to Ambient, Without heatsink	R _{θJA}	26	°C/W
Maximum Thermal Resistance, Junction to Lead, Without heatsink	R _{θJL}	6	°C/W
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	- 40 to + 150	°C

RATING AND CHARACTERISTIC CURVES (LL10XB60HT)

FIG.1 - DERATING CURVE

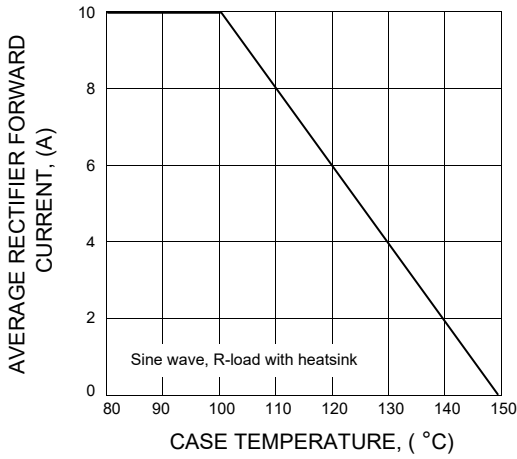


FIG.2 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

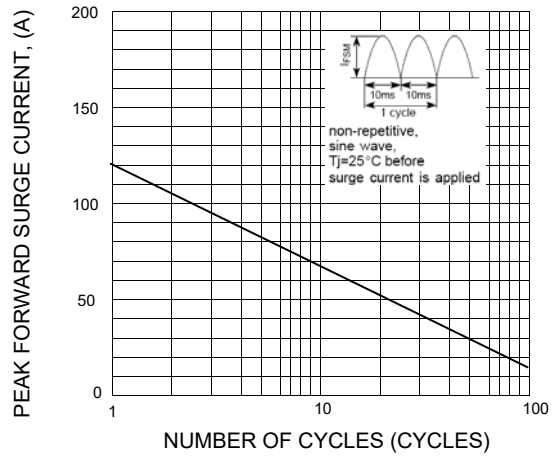


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

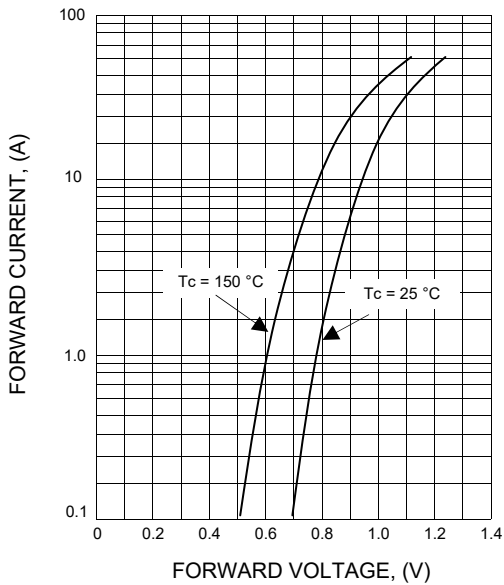


FIG.4 - POWER DISSIPATION

